

Silicon Epitaxial Planar Diode

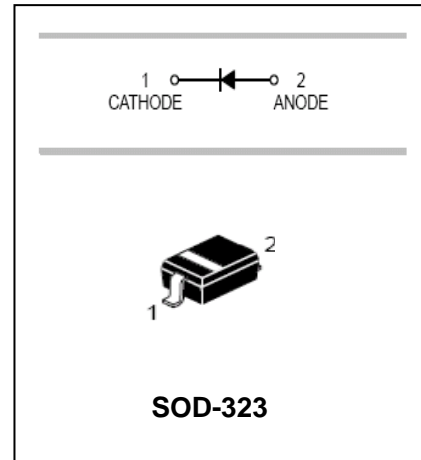
SD107WS

FEATURES

- Low forward voltage drop.
- Guard ring die construction for transient protection.
- Ideal for low logic level applications.
- Low capacitance.



Lead-free



APPLICATIONS

- Schottky barrier switching

ORDERING INFORMATION

Type No.	Marking	Package Code
SD107WS	SG	SOD-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak Repetitive reverse voltage	V_{RRM}	30	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	21	V
Forward continuous Current	I_F	100	mA
Non-Repetitive Peak Forward Surge Current @t ≤10ms	I_{FSM}	750	mA
Power dissipation	P_d	250	mW
Thermal resistance junction to ambient air	$R_{\theta JA}$	500	°C/W
Junction temperature	T_j	150	°C
Storage temperature	T_{STG}	-65~+150	°C

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SD107WS

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)R}$	30			V	$I_R=100\mu A$
Forward voltage	V_F		300		mV	$I_F=2mA$
			360			$I_F=15mA$
			470	550		$I_F=50mA$
			580	800		$I_F=100mA$
Reverse current	I_R			1.0	μA	$V_R=25V$
Capacitance	C_T			7	pF	$V_R=10V, f=1MHz$

PACKAGE OUTLINE

Plastic surface mounted package

SOD-323

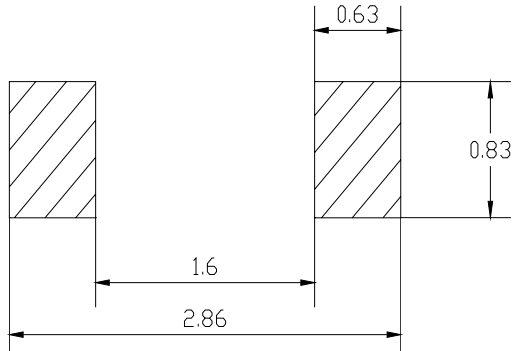
The drawing shows three views of the SOD-323 package: a top view with dimensions K (total length), B (body length), and D (lead width); a side view with dimension C (body thickness); and a bottom view with dimensions J (lead height), E (lead length), and H (lead thickness).

SOD-323		
Dim	Min	Max
A	1.275	1.325
B	1.675	1.725
C	0.9 Typical	
D	0.25	0.35
E	0.27	0.37
H	0.02	0.1
J	0.1 Typical	
K	2.6	2.7
All Dimensions in mm		

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SD107WS

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
SD107WS	SOD-323	3000/Tape&Reel